

PD1300-130D32-I**Φ5 Stem Type InGaAs PIN-Photodiode**

PD1300-130D32-I is InGaAs PIN-Photodiode featuring excellent responsibility and high photocurrent for near infrared.

This PIN-Photodiode consists of a large chip with Φ1mm dia. of active area mounted on the TO-18 stem and is hermetical sealed by metal can with glass ball lens.

These devices are designed to be high photocurrent gains with an angle of half sensitivity of $\pm 18^\circ$.

<Features>

- High Current
- High Response

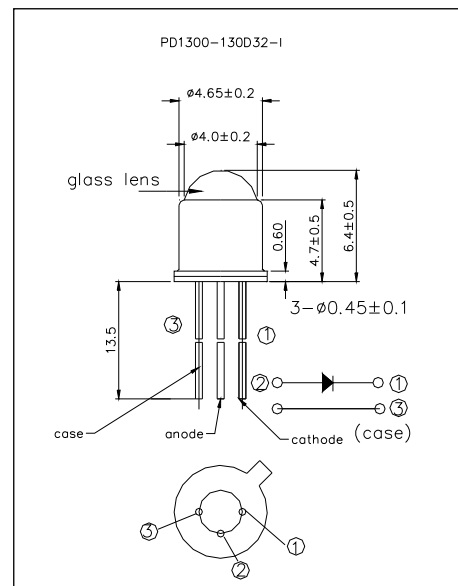
<Specifications>

1. Product Name: InGaAs PIN-Photodio
2. Type Number: PD1300-130D32-I
3. Chip:
 - Active Area: Φ1mm dia.

4.Package

- Type: TO-18 (3pins)
- Lens: Glass Ball Lens
- Cap: Gold Plated

Outer Dimension (Unit:mm)



Absolute Maximum Ratings[Ta=25°C]			
Item	Symbol	Maximum Rated Value	Unit
Reverse Breakdown Voltage	VR	20	V
Operating Temperature	TOPR	-40 ~ +90	°C
Storage Temperature	TSTG	-40 ~ +125	°C
Soldering Temperature*	TSOL	265	°C

* Soldering condition must be completed within 3 seconds at 265°C

Electro-Optical Characteristics [Ta=25°C typ.]						
Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Photo Responsibility	RE	VR=3V, λP =1300nm		0.9		A/W
Photo Current*	IL	VR=3V, λP =1300nm	160			uA
Dark Current	ID	VR=3V		2	20	nA
Spectral Responsibility(Peak)	λP	VR=3V	1000		1550	nm
Half Angle of Sensitivity	θ1/2	VR=0V		± 15		deg
Total Capacitance	CT	F=1MHz, VR=0V		200		pF

* Measured by Epitex's calibrated tool

